

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error	Ref #
1	BRS	16	stack\$ with semiconductor near layer with selective near etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:13				S3
2	BRS	136	semiconductor near layer with selective near etch\$5 and optic\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:14				S4
3	BRS	15	stack\$5 with semiconductor with selective near etch\$5 and optic\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:18				S5
4	BRS	7	stack\$5 with semiconductor with selective with etch\$5 with lateral\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:26				S7
5	BRS	163	semiconductor and selective with etch\$5 with lateral\$4 and optic\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:26				S8
6	BRS	127	semiconductor with layer and selective with etch\$5 with lateral\$4 and optic\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/20 00:26				S9

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors	Ref #
7	BRS	11	semiconductor with layer and selective with etch\$5 with lateral\$4 and optic\$5 and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:40			S10
8	BRS	24	selectiv\$4 with etch\$5 with lateral\$4 and optic\$5 and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:48			S11
9	BRS	4	selectiv\$4 with etch\$5 with lateral\$4 and optic\$5 and fill\$4 with air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:52			S12
10	BRS	7	selectiv\$4 with etch\$5 with lateral\$4 and fill\$4 with air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:50			S13
11	BRS	12	stack with selectiv\$4 with etch\$5 with lateral\$4 and optic\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/27 23:56			S14

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors	Ref #
12	BRS	44	stack with alternat\$4 and selectiv\$4 with etch\$5 with lateral\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:13				S15
13	BRS	146	selectiv\$4 with etch\$5 with lateral\$4 same fill\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:14				S16
14	BRS	22	selectiv\$4 with etch\$5 with lateral\$4 same fill\$5 and optic\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:23				S17
15	BRS	215	etch\$5 with lateral\$4 same fill\$5 and optic\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:23				S18
16	BRS	10	etch\$5 with lateral\$4 same fill\$5 and optic\$4 and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:23				S19
17	BRS	1	stack\$ with selective near etch\$5 near lateral\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:26				S20
18	BRS	2	stack\$4 with selectiv\$4 near etch\$5 near lateral\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:27				S21

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors	Ref #
19	BRS	70	selectiv\$4 near etch\$5 near lateral\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:28				S22
20	BRS	3	("438"/\$).ccls. and stack\$ and selectiv\$ near etch\$5 near lateral\$ and optic\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:41				S24
21	BRS	12	("438"/\$).ccls. and etch\$5 near lateral\$ and optic\$ and vcsel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:44				S25
22	BRS	36	("438"/\$).ccls. and stack\$ near selectiv\$ near etch\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:48				S23
23	BRS	83	epitaxial near liftoff and optic\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:51				S26
24	BRS	19	epitaxial near liftoff and optic\$ and air near gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:51				S27
25	BRS	18	epitaxial near liftoff and etch\$ near lateral\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/28 00:52				S28